

6,468,907 issued October 22, 2002 to Pyo et al., discloses forming a CE layer on a nitride barrier layer surface (e.g., TiN, TaN, WN) with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), and then removing part of the CE layer prior to filling a damascene pattern with a copper (or Al or W) layer using MOCVD. United States Patent No. 6,593,236 issued July 15, 2003 to Pyo et al., discloses forming a CE layer on a nitride barrier layer surface (e.g., TiN, TaN, WN) with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), then removing part of the CE layer while filling a damascene pattern with a copper layer using MOCVD, then electroplating copper. A CE layer of Pyo et al. accelerates or increases the deposition rate of copper onto the CE layer compared to portions of the substrate having no CE layer.

Replacement paragraph, with changes marked as shown:

Pretreating a substrate surface with iodine has been reported to increase the growth rate of copper deposited by a MOCVD technique using Cu(hfac)TMVS precursor. United States Patent No. 6,413,864 issued July 2, 2002 to Pyo et al., discloses forming a copper seed layer [a chemical enhancement layer (CE layer)] on a nitride barrier layer surface (e.g., TiN, TaN, WN), then forming a chemical enhancement layer (CE layer) with an iodine-containing liquid compound prior to forming a first copper [seed] layer by MOCVD, and then electroplating a second copper layer onto the [seed] first copper layer. United States Patent No. 6,468,907 issued October 22, 2002 to Pyo et al., discloses forming a CE layer on a nitride barrier layer surface (e.g., TiN, TaN, WN) with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), and then removing part of the CE layer prior to filling a damascene pattern with a copper (or Al or W) layer using MOCVD. United States Patent No. 6,593,236 issued July 15, 2003 to Pyo et al., discloses forming a CE layer on a [nitride barrier layer surface (e.g., TiN, TaN, WN)] copper seed layer with an iodine-containing liquid or gas (or F, Cl, Br, I or At gas), then removing part of the CE layer by plasma while partially filling a damascene pattern with a copper layer using MOCVD, then electroplating copper. A CE layer of Pyo et al. accelerates or increases the deposition rate of copper onto the CE layer compared to portions of the substrate having no CE layer.

A clean replacement paragraph, without markings, for page 3, starting at line 1, of the specification is included on the following separate sheet: